

2SK3000

Silicon N Channel MOS FET
Low Frequency Power Switching

HITACHI

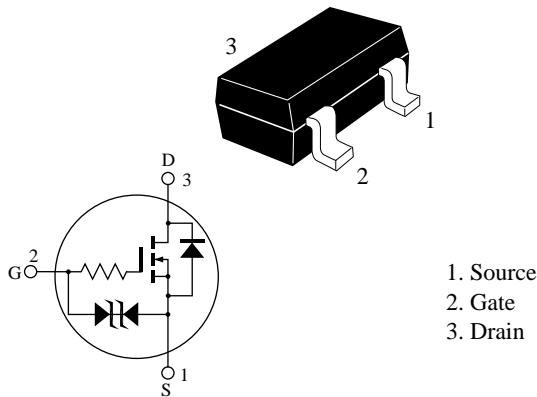
ADE-208-585A (Z)
2nd. Edition
Mar. 2001

Features

- Low on-resistance
 $R_{DS(on)} = 0.25\Omega$ typ. ($V_{GS} = 10\text{ V}$, $I_D = 450\text{ mA}$)
- 4V gate drive devices.
- Small package (MPAK)
- Expansive drain to source surge power capability

Outline

MPAK



Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	40	V
Gate to source voltage	V_{GSS}	± 10	V
Drain current	I_{D}	1.0	A
Drain peak current	$I_{\text{D(pulse)}}^{\text{Note1}}$	4.0	A
Reverse drain current	I_{DR}	1.0	A
Channel dissipation	$P_{\text{ch}}^{\text{Note2}}$	400	mW
Channel temperature	T_{ch}	150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Note: 1. $PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$
2. When using the glass epoxy board (10 mm x 10 mm x 1 mm^t)

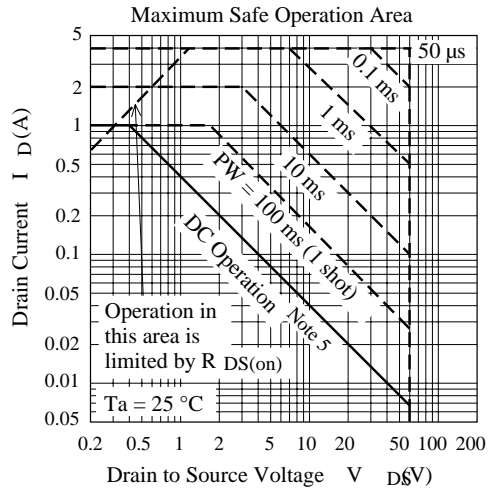
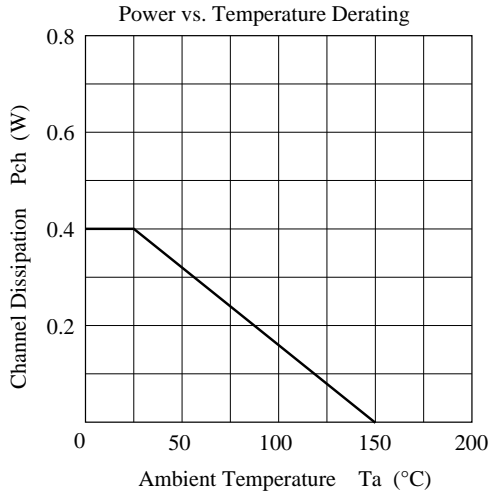
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	40	—	60	V	$I_D = 100\mu A, V_{GS} = 0$
Drain to source voltage	$V_{DS(SUS)}$	40	—	—	V	$L = 100\mu H, I_D = 3 A$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 10	—	—	V	$I_G = \pm 100\mu A, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 40 V, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 5	μA	$V_{GS} = \pm 6.5V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.1	—	2.1	V	$I_D = 10\mu A, V_{DS} = 5V$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.3	0.5	Ω	$I_D = 450 mA$ $V_{GS} = 4V$ ^{Note3}
Static drain to source on state resistance	$R_{DS(on)}$	—	0.25	0.3	Ω	$I_D = 450 mA$ $V_{GS} = 10V$ ^{Note3}
Forward transfer admittance	$ y_{fs} $	0.5	1.2	—	S	$I_D = 450 mA$ $V_{DS} = 10V$ ^{Note3}
Input capacitance	C_{iss}	—	14.0	—	pF	$V_{DS} = 10V$
Output capacitance	C_{oss}	—	68	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	3.0	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	0.12	—	μs	$V_{GS} = 4V, I_D = 450 mA$
Rise time	t_r	—	0.6	—	μs	$R_L = 22\Omega$
Turn-off delay time	$t_{d(off)}$	—	1.7	—	μs	
Fall time	t_f	—	1.4	—	μs	

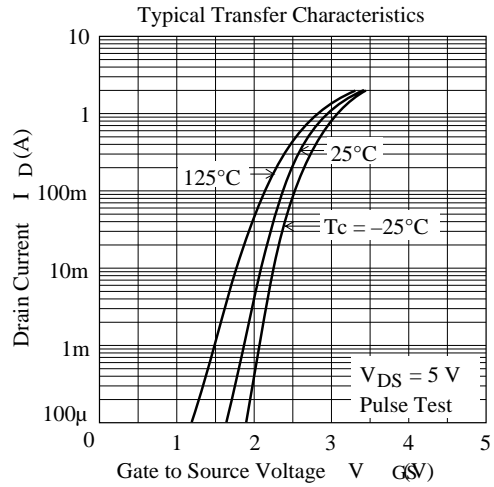
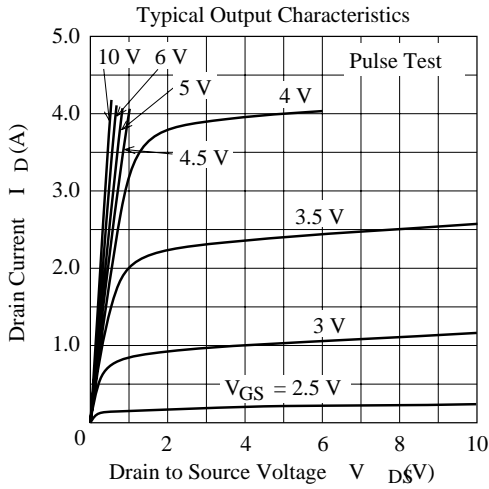
Note: 3. Pulse test

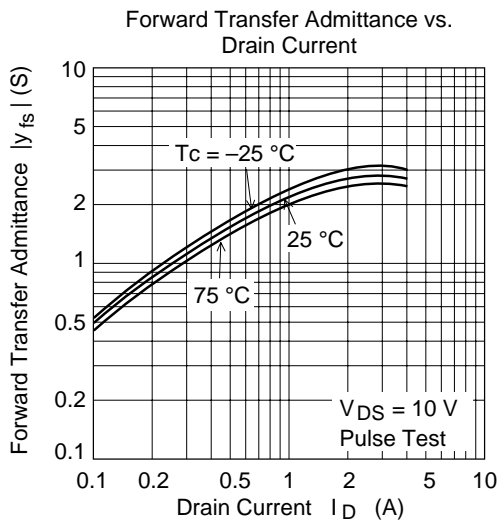
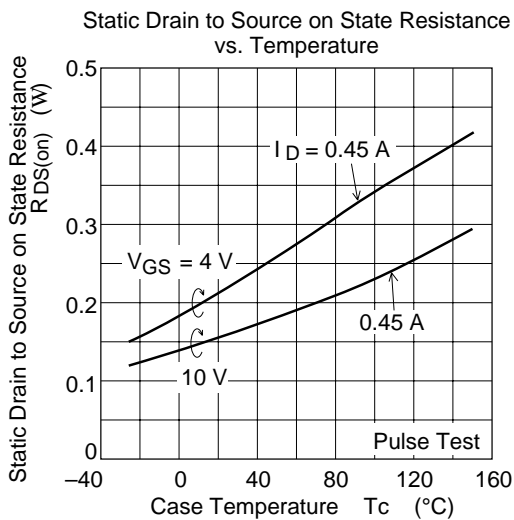
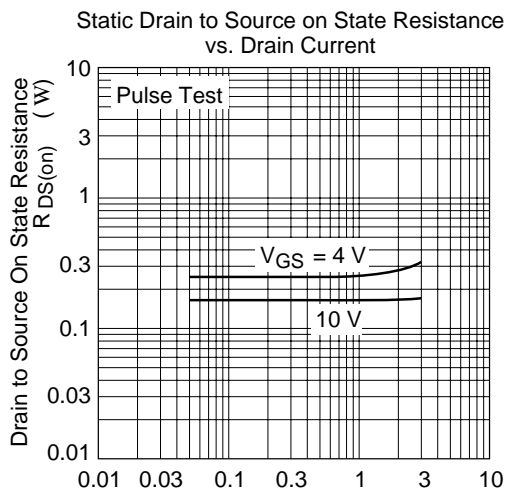
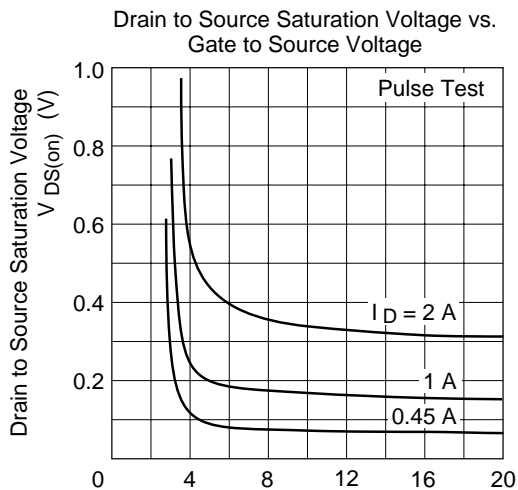
4. Marking is "ZY-".

Main Characteristics

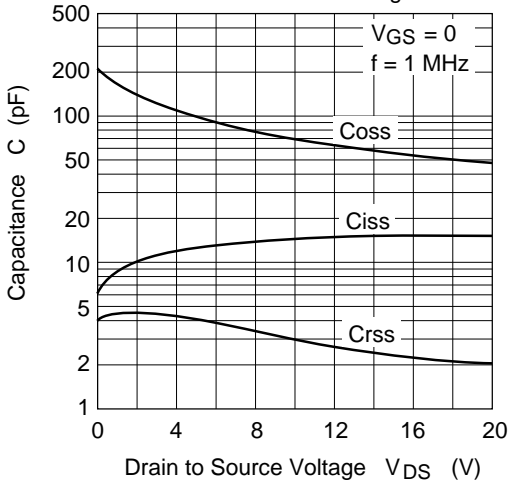


Note5 : When using the glass epoxy (10mm x 10mm x 1mm)

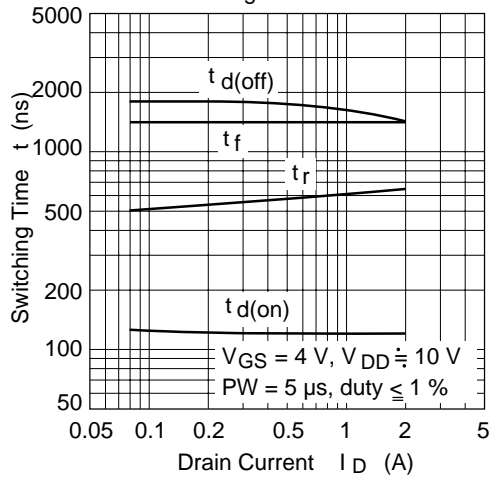




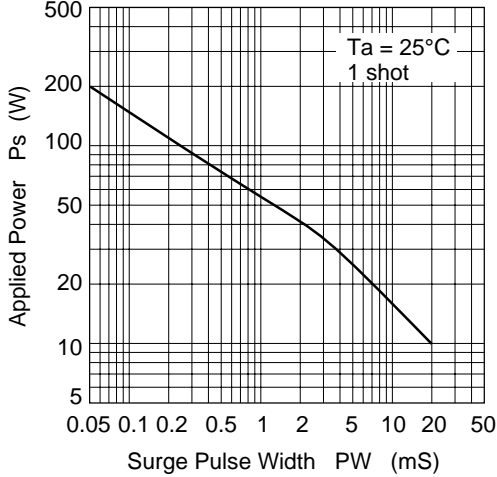
Typical Capacitance vs. Drain to Source Voltage



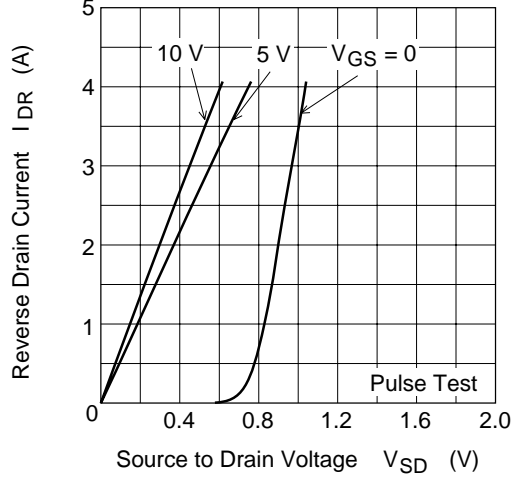
Switching Characteristics



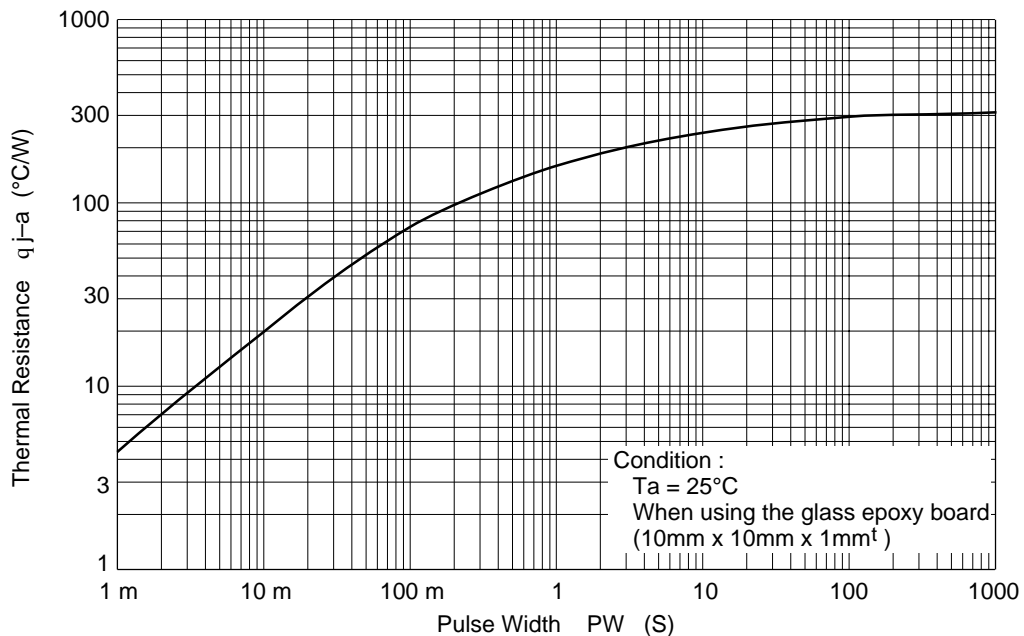
Drain to Source Diode Reverse Surge Destruction Characteristics



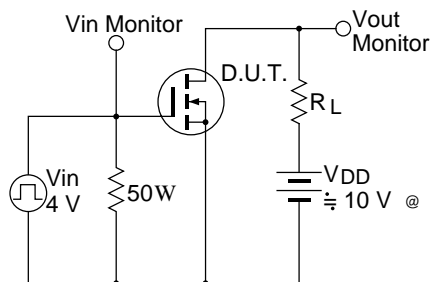
Reverse Drain Current vs. Source to Drain Voltage



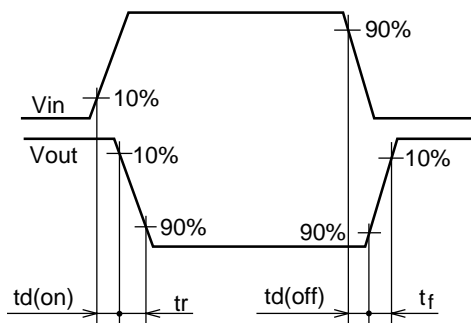
Transient Thermal Resistance



Switching Time Test Circuit



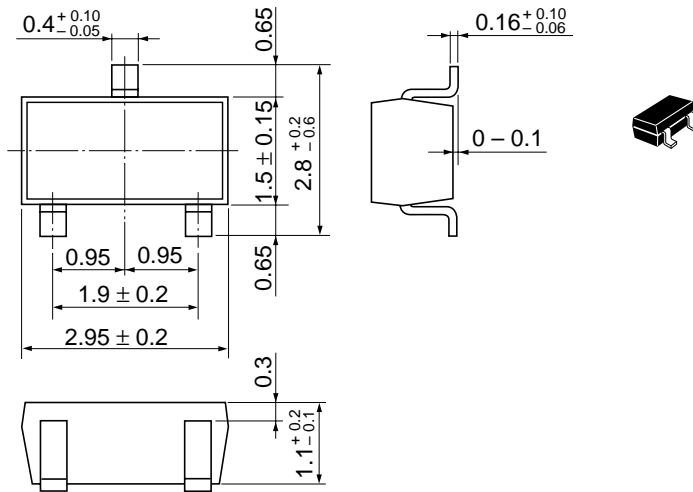
Switching Time Waveforms



Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.011 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://www.hitachi.com.hk>

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